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MOS FET

### FL5252050R

# **Panasonic**

## FL5252050R

Silicon P-channel MOSFET(FET) Silicon epitaxial planar type(SBD)

For switching For DC-DC Converter

#### ■ Features

- Low drain-source ON resistance : RDS (on) typ. = 100 m $\Omega$  ( VGS = -4.0 V )
- Low drive voltage : 2.5 V drive
- Halogen-free / RoHS compliant (EU RoHS / UL-94 V-0 / MSL:Level 1 compliant)

■ Marking Symbol : Y0

Established: 2011-06-17

: 2013-10-28

Revised

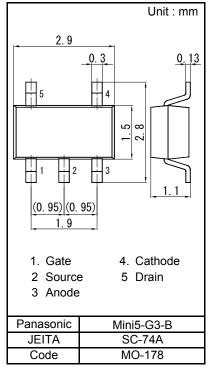
#### ■ Packaging

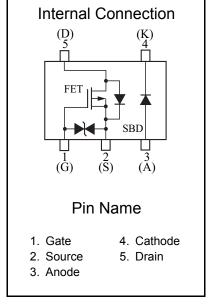
Embossed type (Thermo-compression sealing) 3 000 pcs / reel (standard)

■ Absolute Maximum Ratings Ta = 25 °C

| 項目      |                               | Symbol | Rating      | Unit |  |
|---------|-------------------------------|--------|-------------|------|--|
| FET     | Drain to Source Voltage       | VDS    | -20         | V    |  |
|         | Gate to Source Voltage        | VGS    | ±10         | V    |  |
|         | Drain current                 | ID     | -2.1        | Α    |  |
|         | Drain Current (Pulsed)        | IDp    | -8          | Α    |  |
|         | Channel temperature           | Tch    | 125         | °C   |  |
| SBD     | Reverse voltage               | VR     | 20          | V    |  |
|         | Forward current (Average)     | IF(AV) | 700         | mA   |  |
|         | Junction temperature          | Tj     | 125         | °C   |  |
| Overall | Total power dissipation *1    | PD     | 600         | mW   |  |
|         | Operating ambient temperature | Topr   | -40 to + 85 | °C   |  |
|         | Storage temperature           | Tstg   | -55 to +125 | °C   |  |

Note: \*1 Measuring on ceramic substrate at 40 mm × 38 mm × 0.1 mm
PD absolute maximum rating without a heat shink: 300 mW





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FL5252050R

■ Electrical Characteristics Ta = 25 °C ± 3 °C FET (P-ch.)

| Parameter                          | Symbol   | Conditions                       | Min  | Тур   | Max  | Unit |
|------------------------------------|----------|----------------------------------|------|-------|------|------|
| Drain to Source Breakdown Voltage  | VDSS     | ID = -1 mA, VGS = 0              | -20  |       |      | V    |
| Zero Gate Voltage Drain Current    | IDSS     | VDS = -20 V, VGS = 0             |      |       | -1.0 | μΑ   |
| Gate-source Leakage Current        | IGSS     | $VGS = \pm 8 \text{ V}, VDS = 0$ |      |       | ±10  | μA   |
| Gate-source Threshold Voltage      | Vth      | ID = -1.0 mA, VDS = -10 V        | -0.4 | -0.85 | -1.3 | V    |
| Drain-source On-State Resistance   | RDS(on)1 | ID = -1.0 A, VGS = -4.0 V        |      | 100   | 130  | mΩ   |
| Dialii-source Oil-State Resistance | RDS(on)2 | ID = -0.5 A, VGS = -2.5 V        |      | 130   | 200  |      |
| Forward transfer admittance        | Yfs      | ID = -1.0 A, VDS = -10 V         | 3.0  |       |      | S    |
| Input Capacitance                  | Ciss     |                                  |      | 400   |      | pF   |
| Output Capacitance                 | Coss     | VDS = -10 V, VGS = 0, f = 1 MHz  |      | 40    |      | pF   |
| Reverse Transfer Capacitance       | Crss     |                                  |      | 35    |      | pF   |
| Turn-on time <sup>*1</sup>         | ton      | VDD = -10 V, VGS = 0 to -4 V     | 35   |       |      | ns   |
| Turn-on time                       |          | ID = -1.0 A                      |      |       |      |      |
| Turn-off time <sup>*1</sup>        | toff     | VDD = -10 V, VGS = -4 to 0 V     | 100  |       |      | ns   |
| rum-on ume                         |          | ID = -1.0 A                      |      |       |      |      |

Note: 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 Measuring methods for transistors.

#### **SBD**

| Parameter             | Symbol | Conditions                    | Min | Тур | Max  | Unit |
|-----------------------|--------|-------------------------------|-----|-----|------|------|
| Forward voltage       | VF     | IF = 700 mA                   |     |     | 0.45 | V    |
| Reverse current       | IR     | VR = 20 V                     |     |     | 200  | μA   |
| Terminal capacitance  | Ct     | VR = 10 V, f = 1 MHz          |     | 12  |      | pF   |
| Reverse recovery time | trr    | IF = IR = 100 mA, Irr = 10 mA |     | 4.3 |      | ns   |

Note: Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7031 Measuring methods for diodes.

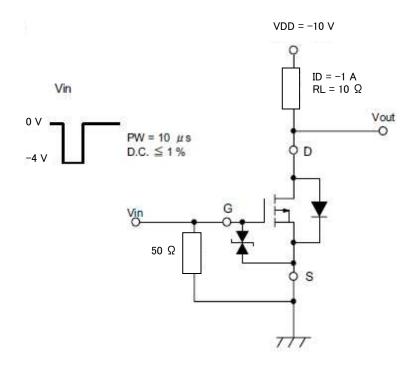
Established: 2011-06-17 : 2013-10-28 Revised

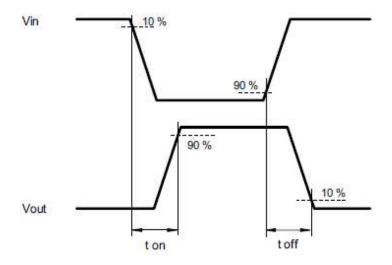
<sup>2. \*1</sup> Turn-on, Turn-off measurement circuit

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\*1 Turn-on, Turn-off measurement circuit





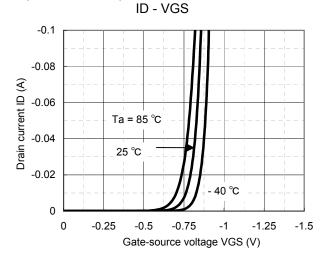
Revision. 3

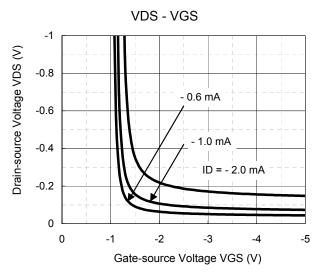
MOS FET

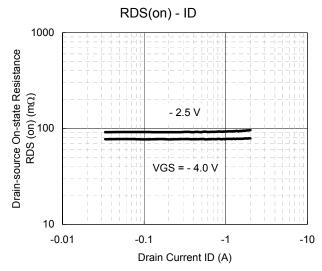
## FL5252050R

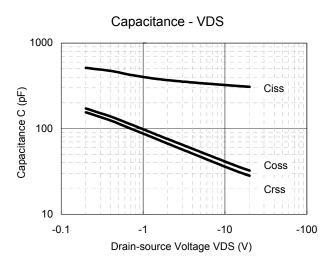
## Technical Data (reference)

ID - VDS -2 - 4.0 V 2.0 V -1.5 Drain current ID (A) VGS = - 1.5 V -1 -0.5 - 1.0 V 0 0 -0.1 -0.2 -0.3 -0.4 -0.5 -0.6 Drain-source voltage VDS (V)









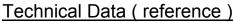
Established: 2011-06-17

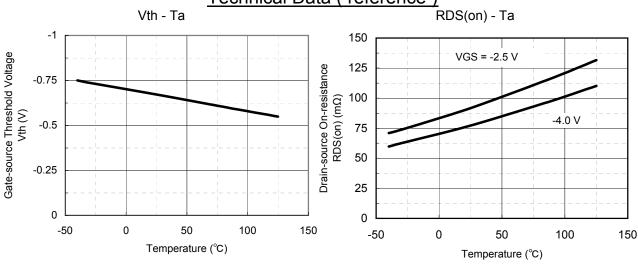
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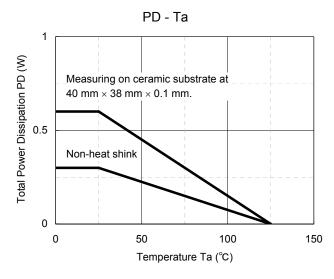
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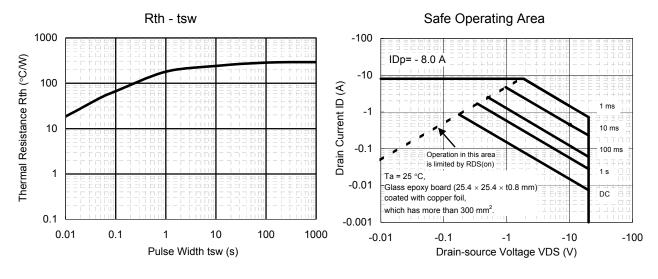
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FL5252050R









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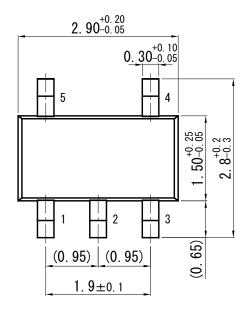
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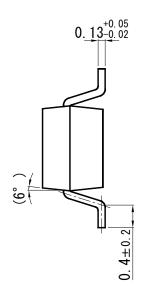
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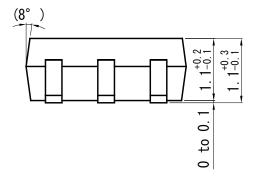
# **Panasonic**

Mini5-G3-B

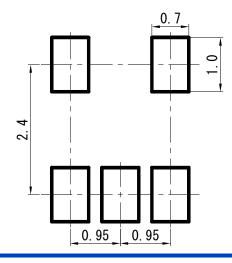
Unit: mm







#### ■ Land Pattern (Reference) (Unit: mm)



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